S1P03R170HBG-C Preliminary

1700V SiC Power MOSFET Module

1 Maximum ratings

Table 1 **Maximum rating** (Tc = 25°C unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
$V_{DS,max}$	Drain source voltage	1700	V	V_{GS}	

2 Packaging characteristics

Table 2 Package characteristics

Symbol	Description	Value	Unit	Note
R_{HS}	High-side Resistance	2.5	mΩ	
R_{LS}	Low-side Resistance	2.5		
Ls	Stray inductance	18	nH	

[1] Not subject to production test. Parameter verified by design/characterization.

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Datasheet

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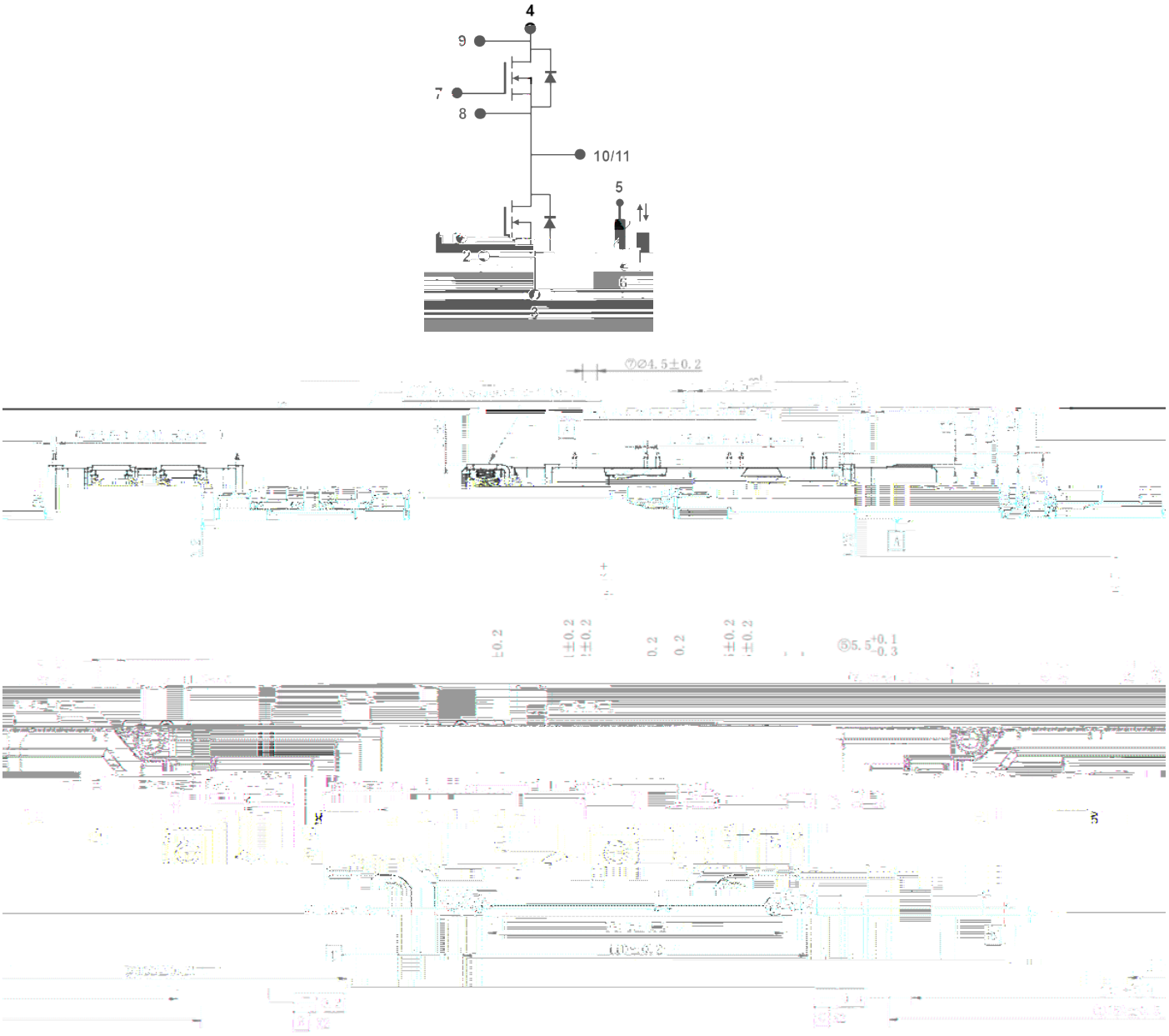
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Figure 7. Threshold voltage VS. T_J

Figure 8. Capacitance VS. V_{DS}

Figure 9. Capacitance VS. V_{DS}

5 Package drawing



Revision history

Document

7. Except as otherwise explicitly approved by Sichain in a written document signed by authorized representatives of Sichain, Sichain' products may not be used in any applications where a failure of the product or any consequences of the use thereof can reasonably be expected to result in personal injury.

8. For use of our products in applications requiring a high degree of reliability (as exemplified below), please contact and consult with a Sichain representatives, for example but not limited to: transportation equipment, primary communication equipment, traffic lights, fire/crime prevention, safety equipment, medical systems, and power transmission systems.